

## 2SK2568

Silicon N Channel MOS FET

REJ03G1017-0300  
(Previous: ADE-208-1363)  
Rev.3.00  
Sep 07, 2005

### Application

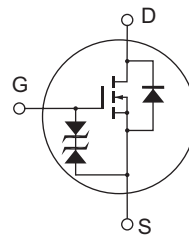
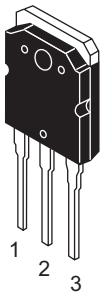
High speed power switching

### Features

- Low on-resistance
- High speed switching
- Low drive current
- Suitable for switching regulator and DC-DC converter

### Outline

RENESAS Package code: PRSS0004ZE-A  
(Package name: TO-3P)



1. Gate
2. Drain  
(Flange)
3. Source

## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DS}$	500	V
Gate to source voltage	$V_{GS}$	$\pm 30$	V
Drain current	$I_D^{*2}$	12	A
Drain peak current	$I_{D(pulse)}^{*1}$	48	A
Body to drain diode reverse drain current	$I_{DR}^{*2}$	12	A
Channel dissipation	$P_{ch}^{*2}$	100	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1.  $PW \leq 10 \mu s$ , duty cycle  $\leq 1 \%$   
 2. Value at  $T_c = 25^\circ C$

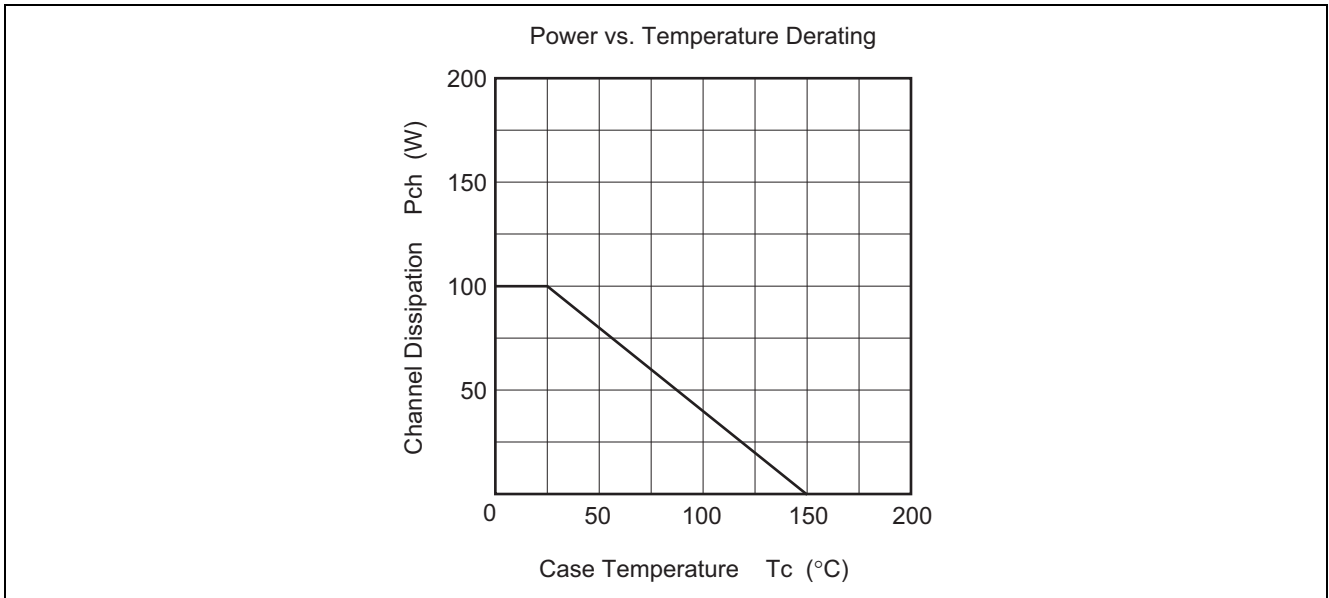
## Electrical Characteristics

(Ta = 25°C)

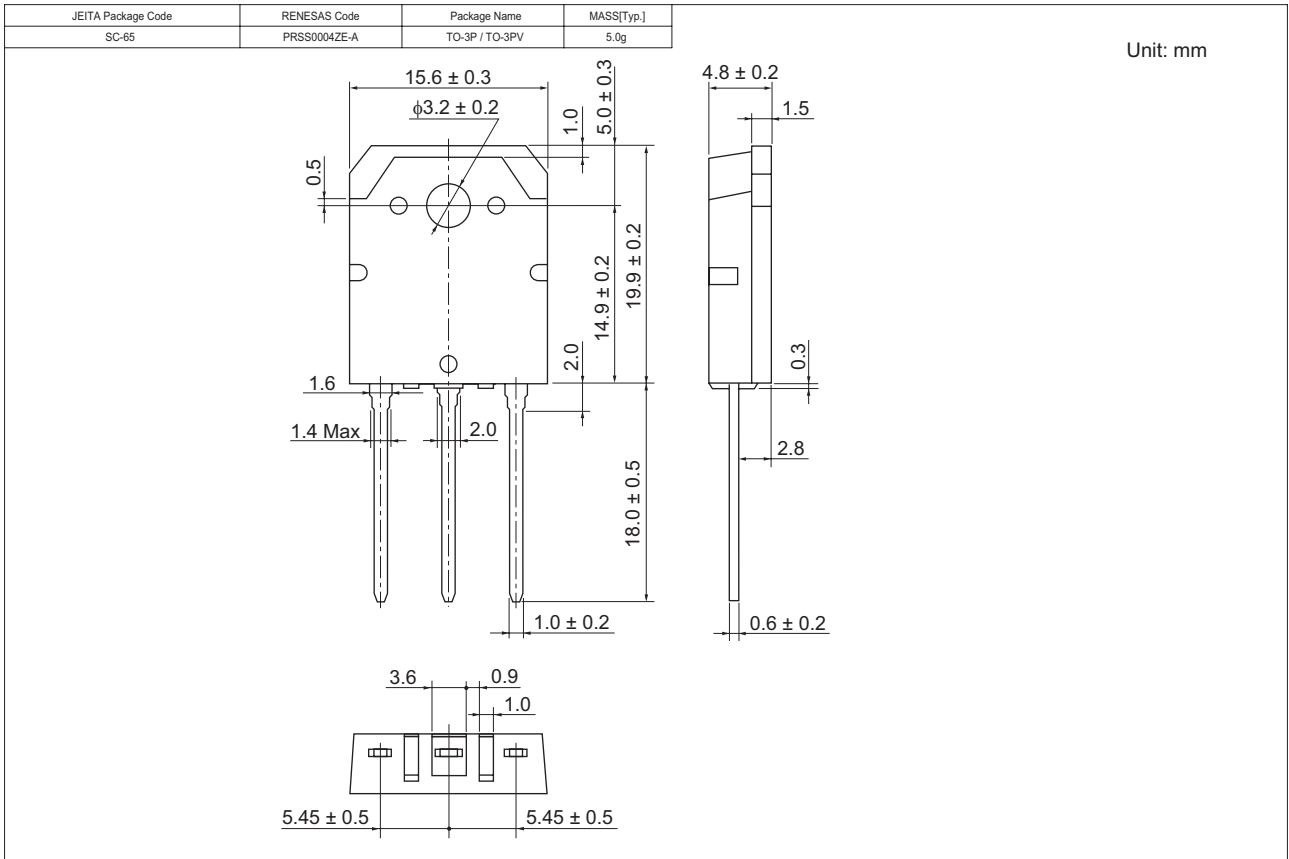
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DS}$	500	—	—	V	$I_D = 10 \text{ mA}$ , $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GS}$	$\pm 30$	—	—	V	$I_G = \pm 100 \mu A$ , $V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	$\pm 10$	$\mu A$	$V_{GS} = \pm 25 \text{ V}$ , $V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	250	$\mu A$	$V_{DS} = 400 \text{ V}$ , $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	—	3.0	V	$I_D = 1 \text{ mA}$ , $V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.5	0.6	$\Omega$	$I_D = 6 \text{ A}$ , $V_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	6.0	10	—	S	$I_D = 6 \text{ A}$ , $V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	$C_{iss}$	—	1560	—	pF	$V_{DS} = 10 \text{ V}$ , $V_{GS} = 0$ , $f = 1 \text{ MHz}$
Output capacitance	$C_{oss}$	—	450	—	pF	
Reverse transfer capacitance	$C_{rss}$	—	72	—	pF	
Turn-on delay time	$t_{d(on)}$	—	22	—	ns	$I_D = 6 \text{ A}$ , $V_{GS} = 10 \text{ V}$ , $R_L = 5 \Omega$
Rise time	$t_r$	—	78	—	ns	
Turn-off delay time	$t_{d(off)}$	—	140	—	ns	
Fall time	$t_f$	—	60	—	ns	
Body to drain diode forward voltage	$V_{DF}$	—	1.1	—	V	$I_F = 12 \text{ A}$ , $V_{GS} = 0$
Body to drain diode reverse recovery time	$t_{rr}$	—	105	—	ns	$I_F = 12 \text{ A}$ , $V_{GS} = 0$ $di_F / dt = 100 \text{ A} / \mu s$

Note: 3. Pulse Test

## Main Characteristics



## Package Dimensions



## Ordering Information

Part Name	Quantity	Shipping Container
2SK2568-E	360 pcs	Box (Tube)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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